Sputtered Gold as an Effective Schottky Gate for Strained Si/SiGe Nanostructures

GAVIN SCOTT, MING XIAO, UCLA Dept of Physics, ED CROKE, HRL Laboratories, ELI YABLOMOVITCH, UCLA Dept of Electrical Engineering, HONGWEN JIANG, UCLA Dept of Physics — Metallization of Schottky surface gates by sputtering Au on strained Si/SiGe heterojunctions enables the depletion of the two dimensional electron gas (2DEG) at a relatively small voltage while maintaining an extremely low level of leakage current. A fabrication process has been developed to enable the formation of sub-micron Au electrodes sputtered onto Si/SiGe without the need of a wetting layer.